

## Supplementary Information

### Scalable approach to multi-dimensional bulk Si anodes via metal-assisted chemical etching

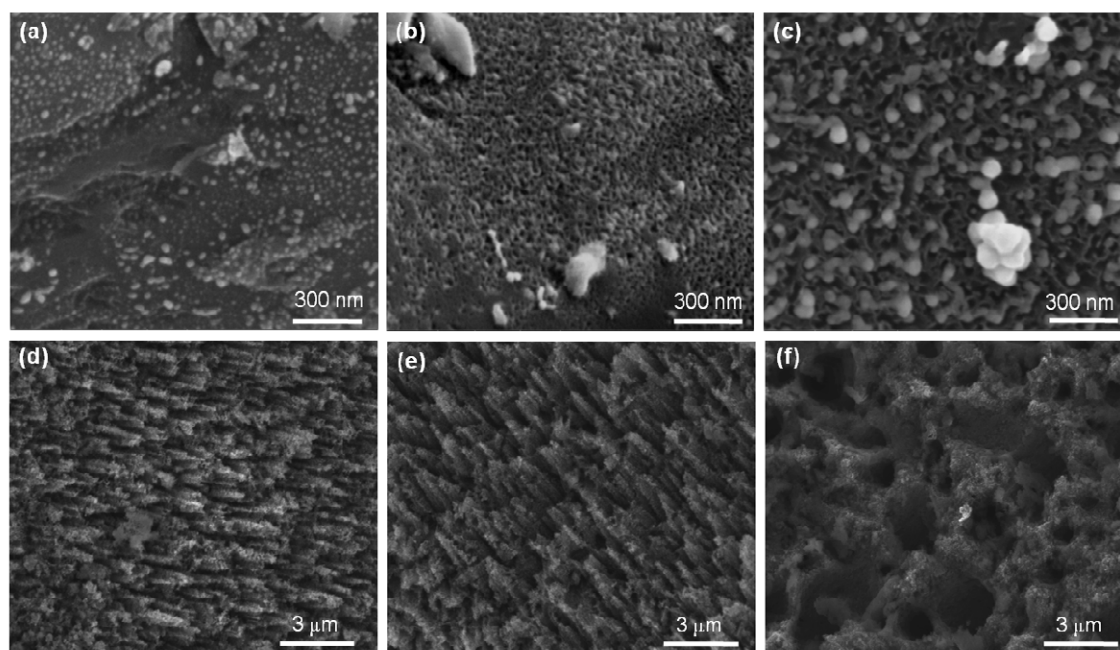
Byoung Man Bang, Hyunjung Kim, Hyun-Kon Song, Jaephil Cho\* and Soojin Park\*

Interdisciplinary School of Green Energy, Ulsan National Institute of Science and  
Technology (UNIST), Ulsan 689-798, Korea

#### 1. Materials and Methods

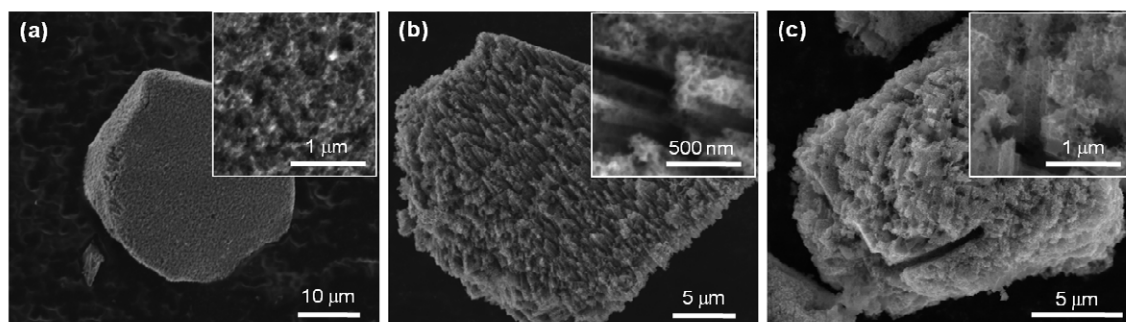
Commercially available Si powder was immersed in a solution of 5-20 mM silver nitrate ( $\text{AgNO}_3$ ) and 5 M HF for a controlled time. Immediately after rinsing, the silver deposited silicon powder was immersed in an etchant consisting of 5 M HF and 1.5%  $\text{H}_2\text{O}_2$  at 50 °C for 1-3 hr to produce silver catalyzed etched Si materials. Depending on the deposition time of silver nitrate, the size of silver particles was varied (Fig. S1(a-c)). During electroless deposition of silver, nanopits were also observed by etching in HF solutions. When the silicon powder having various silver particle sizes was soaked into an etchant, composed of 5 M HF and 1.5%  $\text{H}_2\text{O}_2$ , at 50 °C for 1 hr, nanoporous silicon nanowires, which protrude out from intact silicon core, were produced with different length and pore size (Fig. S1(d-f)). In addition to size of silver catalyst, the concentration of  $\text{H}_2\text{O}_2$  that act as an oxidant is another controllable parameter to tune the Si morphology. As the  $\text{H}_2\text{O}_2$  concentrations of

1.0, 1.5, and 2.0% were used at a fixed HF concentration (5 M), shallow nanopits, Si nanowires, and Si macropores were prepared, respectively (Fig. S2). To obtain multi-dimensional Si powders that nanoporous Si nanowires protrude out from microscale Si matrix, silver deposited Si samples were etched in a 5 M HF and 1.5% H<sub>2</sub>O<sub>2</sub> at 50 °C for 3 hr. As-synthesized Si powders were immersed in 5% HF for 1 min to remove silicon oxide onto the surface of etched Si, and followed by drying in a vacuum oven at 100 °C for 2 hr to remove water completely. Subsequently, the etched Si samples were coated by carbon by thermal decomposition of acetylene gas at 700 °C for 20 min in quartz furnace.



**Fig. S1** Morphologies of Si surfaces according to the size of silver nanoparticles. SEM images of silver deposited Si powders prepared by three different silver nitrate concentrations of (a) 5 mM, (b) 10 mM, and (c) 20 mM. Immediately after silver deposition, the samples were immersed in an etchant consisting of 5 M HF and 1.5% H<sub>2</sub>O<sub>2</sub> at 50 °C for

1 hr to etch the Si surfaces using silver catalyst. SEM images of the samples etched from samples seen in Fig. S1(a-c) show (d) short Si nanowires, (e) long nanoporous Si nanowires, and (f) macroporous Si structures, respectively.

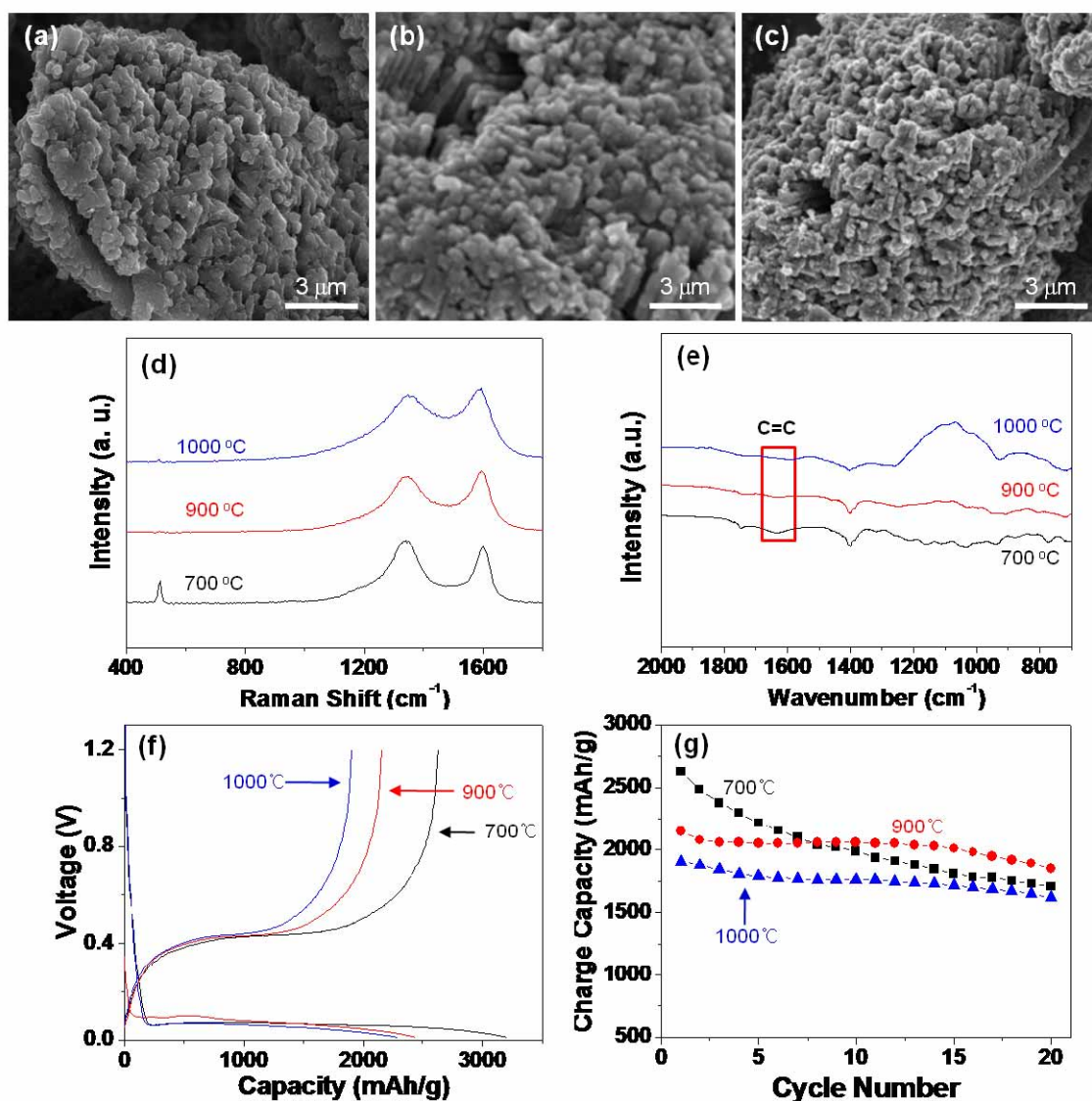


**Fig. S2** Morphologies of Si surfaces according to the concentrations of  $\text{H}_2\text{O}_2$ . SEM images of Si powders chemically etched with three different  $\text{H}_2\text{O}_2$  concentrations of (a) 1.0%, (b) 1.5%, and (c) 2.0% at a fixed HF concentration of 5 M. All samples were silver deposited in 10 mM  $\text{AgNO}_3$  and 5 M HF plating solution for 3 min.  $\text{H}_2\text{O}_2$  acts as an oxidant to etch the Si and the concentration of  $\text{H}_2\text{O}_2$  enables to control the morphologies of Si powder. The corresponding SEM images show that Si nanopits (from 1.0%  $\text{H}_2\text{O}_2$ ), porous Si nanowires (from 1.5%  $\text{H}_2\text{O}_2$ ), and macroporous Si structures (from 2.0%  $\text{H}_2\text{O}_2$ ) were synthesized. The insets show the magnified Si morphologies.

## 2. Effect of carbon-coating temperature on the electrochemical performance of Si electrodes

We investigated the effect of carbon coating condition on the electrochemical performance. The SEM images of mSi carbon-coated at 700, 900, and 1000 °C do not show the distinct difference (Fig. S3(a-c)). Therefore, Raman and FT-IR spectrum were obtained to characterize three different samples. Figure S3d shows the Raman spectra of multi-dimensional Si carbon coated with decomposition of acetylene gas at 700, 900, and 1000 °C. From the two peaks appearing at  $\sim 1360$  (D band) and  $\sim 1580$   $\text{cm}^{-1}$  (G band), the dimensional ratio of the D and G bands of samples carbon coated at 700, 900, and 1000 °C are 2.5, 2.1, and 3.1, respectively. The FT-IR spectrum of sample prepared at relative low temperature (700 °C) shows incomplete decomposition of acetylene molecules appearing at  $\sim 1640$   $\text{cm}^{-1}$ , which is associated with the vibration of carbon (vinyl bonds) skeleton of the sample (Fig. S3(e)). In case of samples coated at 1000 °C, incomplete decomposition of acetylene gas was not observed, but lower degree of graphitization was obtained due to small amount of oxygen remaining carbonization process (Fig. S3(d & e)). All three samples were prepared with a similar carbon content of  $\sim 30\text{wt}\%$  at three different temperatures. In order to compare the electrochemical performance of three samples, galvanostatic discharge/charge experiments were carried out. Figure 6f shows the voltage profiles of the three c-mSi anodes at 0.1 C rate between 1.2 V and 0.01 V. The first cycle discharge capacities are 3200, 2440, and 2290 mAh/g for the electrodes of multi-dimensional Si carbon-coated at 700, 900, and 1000 °C, respectively, with the corresponding first charge capacities of 2630, 2150, and 1900 mAh/g. Therefore, the

coulombic efficiencies in the first cycle are 65%, 88%, and 85% for the three different Si samples carbon-coated at 700, 900, and 1000 °C, respectively. The cycling performance of samples with high degree of graphitization is superior to that of low degree samples (Fig. S3(g)).



**Figure S3.** Effect of carbon-coating temperature on the electrochemical performance. SEM images showing mSi carbon-coated at (a) 700, (b) 900, and (c) 1000 °C. (d) Raman spectra of Si anodes coated with carbon at 700, 900, and 1000 °C. (e) The corresponding FT-IR spectrum of each anode materials. (f) Voltage profiles for the first galvanostatic cycles of the c-mSi at the 0.1 C rate. All three samples have a similar carbon content of ~28 wt%. (g) Charge capacity versus cycle number for the carbon-coated Si at the 0.1 C rate. The carbon coating condition affects the initial capacity and cycling retention. Square, circle, and triangle symbols represent the carbonization temperature of 700, 900, and 1000 °C, respectively.

### Reference

S1. Svatoš, A., & Attygalle, A. B. Characterization of Vinyl-Substituted, Carbon-Carbon Double Bonds by GC/FT-IR Analysis, *Anal.Chem.* **69**, 1827-1836 (1997).